Abstracts

Measurernent and Analysis of GaAs MESFET Parasitic Capacitances (Short Papers)

R. Anholt and S. Swirhun. "Measurernent and Analysis of GaAs MESFET Parasitic Capacitances (Short Papers)." 1991 Transactions on Microwave Theory and Techniques 39.7 (Jul. 1991 [T-MTT]): 1247-1251.

From S-parameter measurements and subsequent equivalent circuit parameter extraction for a series of 0.25 µm, ion-implanted GaAs MESFET's with different widths and different gate-source drain-source spacings, parasitic FET pad capacitances and interelectrode capacitances have been separated from active-FET capacitances. The active-FET fringe capacitances extracted at pinch-off are with results from two-dimensional Poisson simulations.

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